

 <p>Диодные мосты однофазные KBPC</p>	 <p>Диодные мосты однофазные QL</p>	 <p>Диодные мосты трёхфазные SQL</p>	 <p>Диодные мосты однофазные MDQ</p>
 <p>Диодные мосты трёхфазные MDE</p>	 <p>Диодные мосты однофазные DF10M</p>	Минск www.fotorele.net www.tristor.by email minsk17@tut.by tel.+375447584780 и другие, радиодетали, электронные компоненты каталог, описание, технические, характеристики, datasheet, параметры, маркировка, габариты, фото, аналог, замена смотрите ниже	



QR код

S25VB10, S25VB20, S25VB40, S25VB60, S25VB80, S25VB100,

**s25vb100 диодный мост, Минск
продажа, купить,
однофазный
выпрямитель
диодный мост**

S25VB10, S25VB20, S25VB40, S25VB60, S25VB80, S25VB100,

**диодный мост s25vb100 характеристики
диодный мост s25vb100 купить
диодный мост s25vb100 даташит
диодный мост s25vb100 аналог
диодный мост s25vb100 параметры
диодный мост s25vb100 для сварочного аппарата
диодный мост s25vb100 цена
диодный мост s25vb100x для инверт сварки кедр
диодный мост s25vb100 купить Беларусь
для сварочного инвертора
s25vb100 характеристики**

s25vb100 аналог

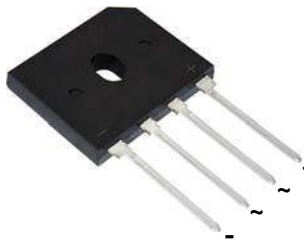
s25vb100 цена

s25vb100 как проверить

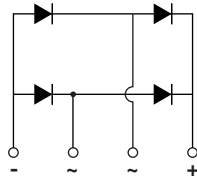
**s35vb100 характеристики
S25VB100 25A 1000V**



Glass Passivated Single-Phase Bridge Rectifier



Case Style GBU



Case Style GBU

FEATURES

- UL recognition file number E54214
- Ideal for printed circuit boards
- High surge current capability
- High case dielectric strength of 1500 V_{RMS}
- Solder dip 275 °C max. 10 s, per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT

TYPICAL APPLICATIONS

General purpose use in AC/DC bridge full wave rectification for monitor, TV, printer, power supply, switching mode power supply, adapter, audio equipment, and home appliances applications.

MECHANICAL DATA

- Case:** GBU
Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS-compliant, commercial grade
- Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102
E3 suffix meets JESD 201 class 1A whisker test
- Polarity:** As marked on body
- Mounting Torque:** 10 cm-kg (8.8 inches-lbs) max.
- Recommended Torque:** 5.7 cm-kg (5 inches-lbs)

PRIMARY CHARACTERISTICS	
Package	GBU
I _{F(AV)}	8.0 A
V _{RRM}	50 V, 100 V, 200 V, 400 V, 600 V, 800 V, 1000 V
I _{FSM}	200 A
I _R	5 μA
V _F at I _F = 8.0 A	1.0 V
T _J max.	150 °C
Diode variations	In-Line

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)									
PARAMETER	SYMBOL	GBU8A	GBU8B	GBU8D	GBU8G	GBU8J	GBU8K	GBU8M	UNIT
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified output current at	T _C = 60 °C	I _{F(AV)} ⁽¹⁾							A
	T _A = 40 °C	I _{F(AV)} ⁽²⁾							
Peak forward surge current single sine-wave super-imposed on rated load	I _{FSM}	200							A
Rating for fusing (t < 8.3 ms)	I ² t	166							A ² s
Operating junction and storage temperature range	T _J , T _{STG}	-55 to +150							°C

Notes

- (1) Unit case mounted on aluminum plate heatsink
- (2) Units mounted on PCB with 0.5" x 0.5" (12 mm x 12 mm) copper pads and 0.375" (9.5 mm) lead length



ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

PARAMETER	TEST CONDITIONS	SYMBOL	GBU8A	GBU8B	GBU8D	GBU8G	GBU8J	GBU8K	GBU8M	UNIT
Maximum instantaneous forward voltage drop per diode	8.0 A	V_F				1.0				V
Maximum DC reverse current at rated DC blocking voltage per diode	$T_A = 25\text{ }^\circ\text{C}$	I_R				5.0				μA
	$T_A = 125\text{ }^\circ\text{C}$					500				
Typical junction capacitance per diode	4 V, 1 MHz	C_J				68				pF

THERMAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	GBU8A	GBU8B	GBU8D	GBU8G	GBU8J	GBU8K	GBU8M	UNIT
Typical thermal resistance	$R_{\theta JA}^{(2)}$				20				$^\circ\text{C/W}$
	$R_{\theta JC}^{(1)(3)}$				4.0				

Notes

- (1) Units case mounted on aluminum plate heatsink
- (2) Units mounted in free air, no heatsink on PCB, 0.5" x 0.5" (12 mm x 12 mm) copper pads, 0.375" (9.5 mm) lead length
- (3) Recommended mounting position is to bolt down on heatsink with silicone thermal compound for maximum heat transfer with #6 screws

ORDERING INFORMATION

PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
GBU8J-E3/45	3.857	45	20	Tube
GBU8J-E3/51	3.857	51	250	Paper tray

RATINGS AND CHARACTERISTICS CURVES ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

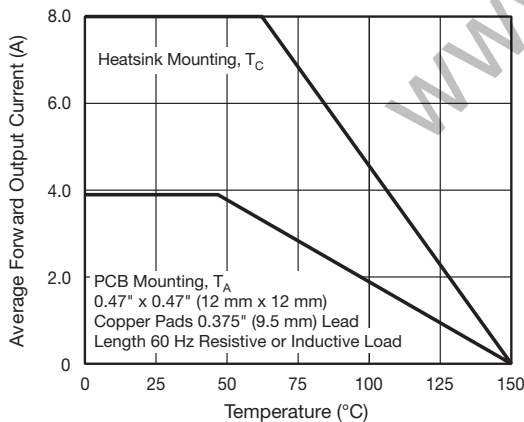


Fig. 1 - Derating Curve Output Rectified Current

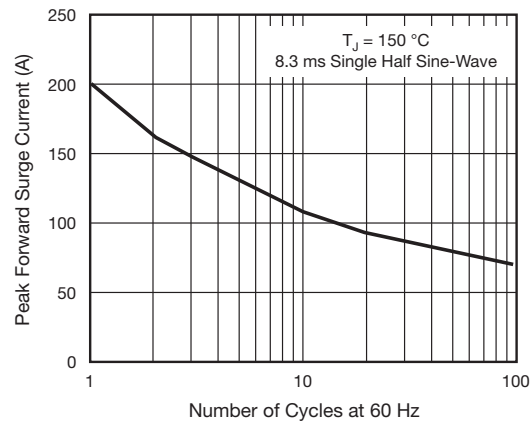


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

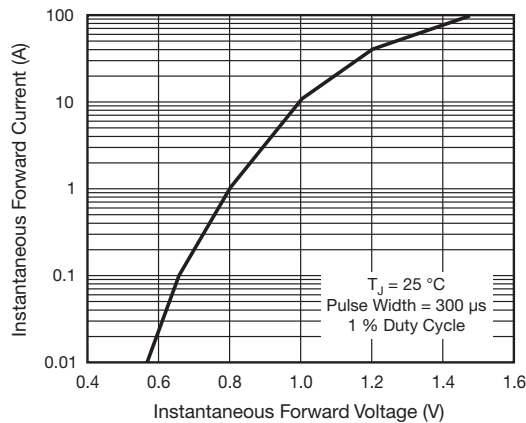


Fig. 3 - Typical Forward Characteristics Per Diode

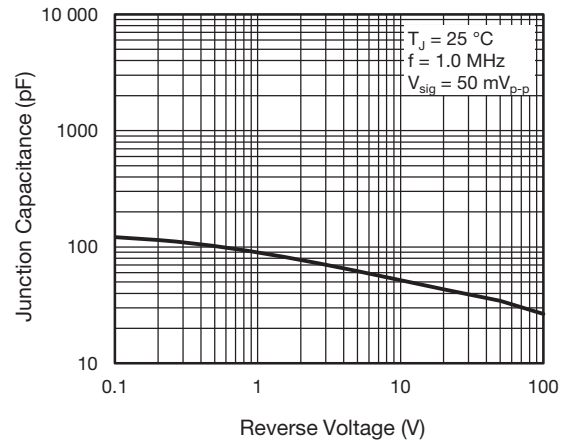


Fig. 5 - Typical Junction Capacitance Per Diode

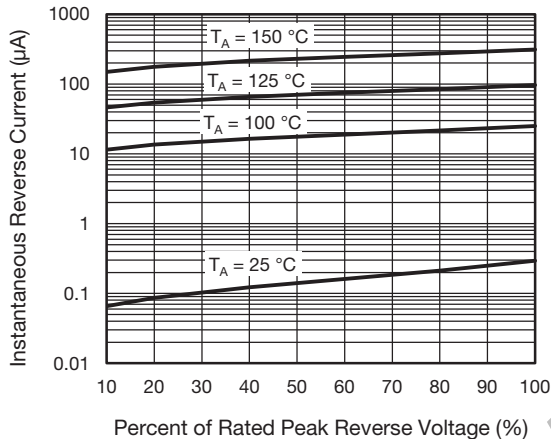


Fig. 4 - Typical Reverse Leakage Characteristics Per Diode

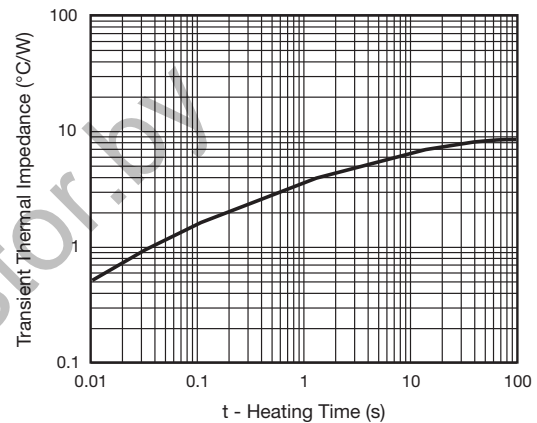
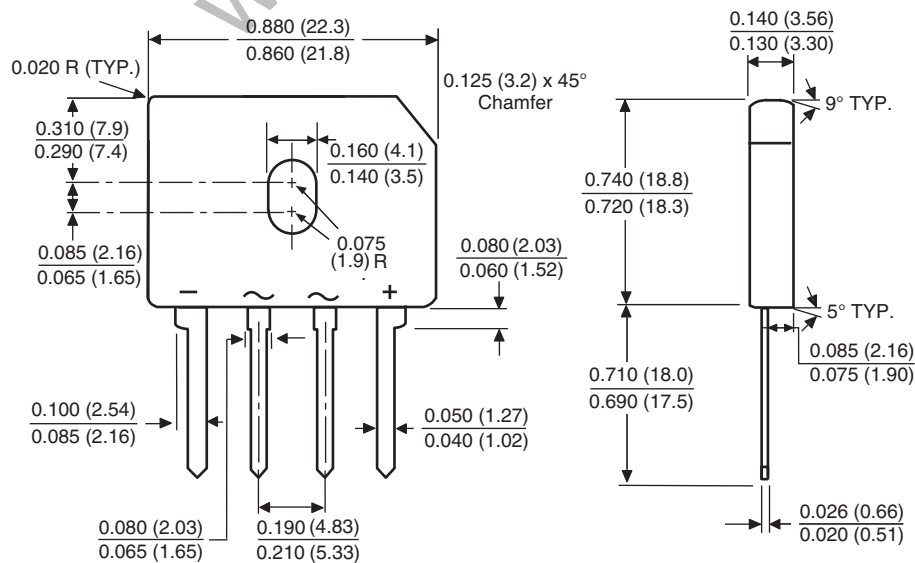


Fig. 6 - Typical Transient Thermal Impedance Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

Case Type GBU



Polarity shown on front side of case, positive lead by beveled corner



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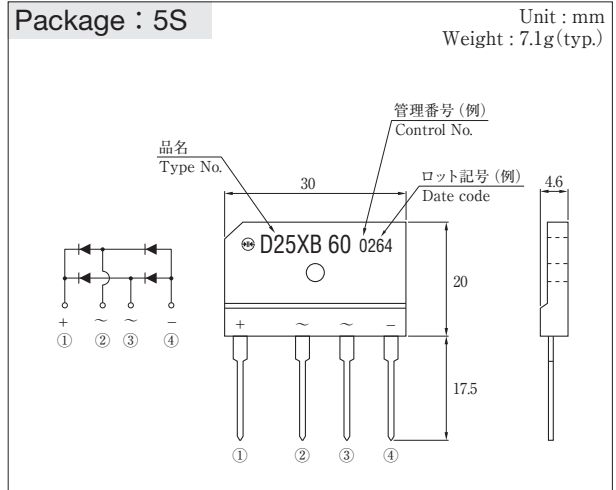
特長

- 薄型 SIP パッケージ
- UL E142422
- 大電流容量
- 高耐圧・高 I_{FSM}
- 高放熱伝導性

Feature

- Thin-SIP
- UL E142422
- Large I_o
- High Voltage・Large I_{FSM}
- High Thermal Radiation

■外観図 OUTLINE



外形図については新電元 Web サイト又は〈半導体製品一覧表〉をご参照下さい。捺印表示については捺印仕様をご確認下さい。
For details of outline dimensions, refer to our web site or the Semiconductor Short Form Catalog. As for the marking, refer to the specification "Marking, Terminal Connection."

■定格表 RATINGS

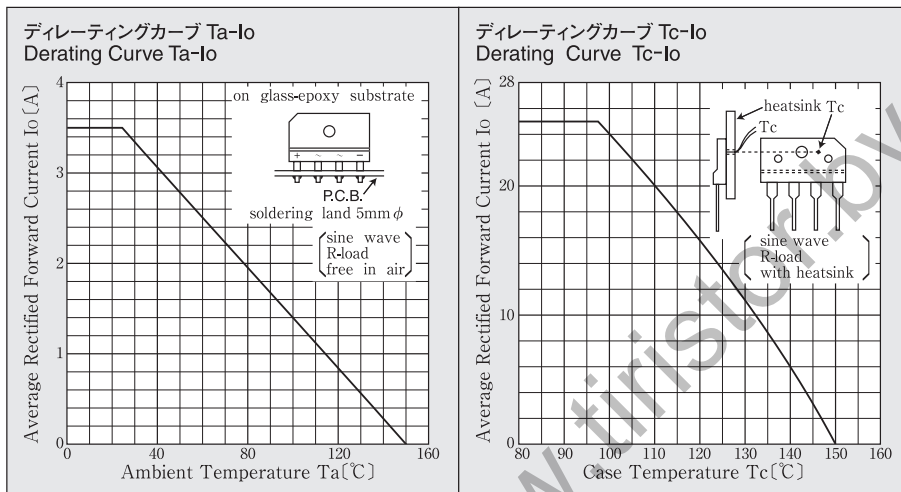
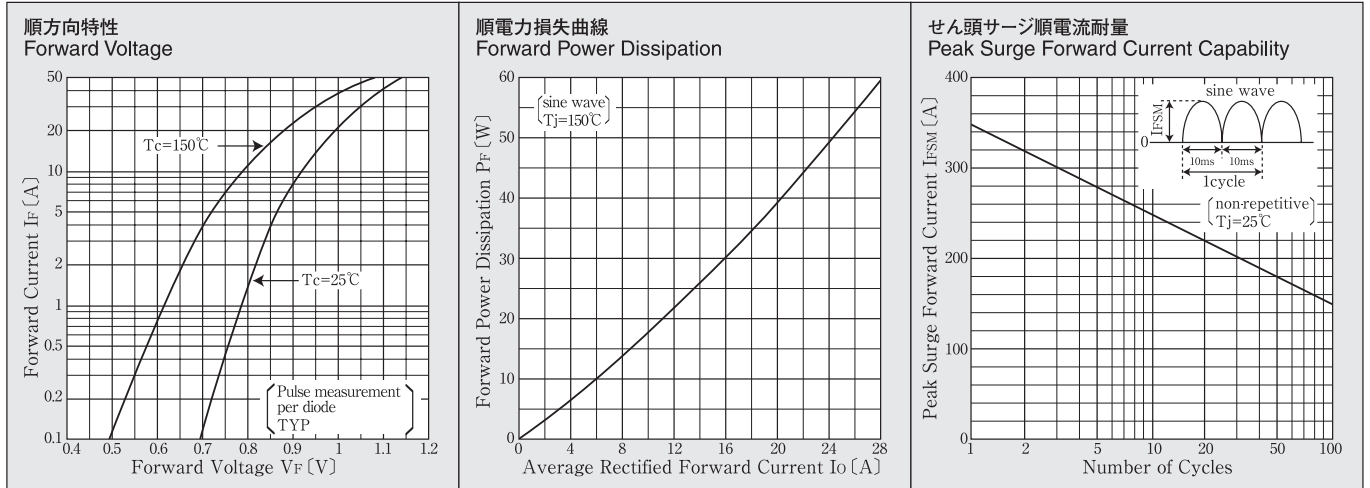
●絶対最大定格 Absolute Maximum Ratings (指定のない場合 T_c=25℃ / unless otherwise specified)

項目 Item	記号 Symbol	条件 Conditions	品名 Type No.	D25XB60	D25XB80	単位 Unit
保存温度 Storage Temperature	T _{stg}			- 40~150		℃
接合部温度 Operation Junction Temperature	T _j			150		℃
せん頭逆電圧 Maximum Reverse Voltage	V _{RM}			600	800	V
出力電流 Average Rectified Forward Current	I _O	50Hz 正弦波, 抵抗負荷 50Hz sine wave, Resistance load	フィン付き With heatsink	T _c = 98℃		A
			フィンなし Without heatsink	T _a = 25℃		
せん頭サージ順電流 Peak Surge Forward Current	I _{FSM}	50Hz 正弦波, 非繰り返し 1 サイクルせん頭値, T _j = 25℃ 50Hz sine wave, Non-repetitive 1 cycle peak value, T _j = 25℃		350		A
電流二乗時間積 Current Squared Time	I ² t	1ms ≤ t < 10ms, T _j = 25℃, 1 素子当たりの規格値 per diode		300		A ² s
絶縁耐圧 Dielectric Strength	V _{dis}	一括端子・ケース間, AC 1 分間印加 Terminals to Case, AC 1 minute		2.5		kV
締め付けトルク Mounting Torque	TOR	(推奨値 : 0.5 N・m) (Recommended torque : 0.5 N・m)		0.8		N・m

●電氣的・熱的特性 Electrical Characteristics (指定のない場合 T_c=25℃ / unless otherwise specified)

順電圧 Forward Voltage	V _F	I _F = 12.5A, パルス測定, 1 素子当たりの規格値 Pulse measurement, per diode		MAX 1.05	V
逆電流 Reverse Current	I _R	V _R = V _{RM} , パルス測定, 1 素子当たりの規格値 Pulse measurement, per diode		MAX 10	μA
熱抵抗 Thermal Resistance	θ _{jc}	接合部・ケース間, フィン付き Junction to Case, With heatsink		MAX 1	℃/W
	θ _{jl}	接合部・リード間, フィンなし Junction to Lead, Without heatsink		MAX 5	
	θ _{ja}	接合部・周囲間, フィンなし Junction to Ambient, Without heatsink		MAX 22	

■特性図 CHARACTERISTIC DIAGRAMS



- * Sine wave は 50Hz で測定しています。
- * 50Hz sine wave is used for measurements.
- * 半導体製品の特性は一般的にバラツキを持っています。
- Typical は統計的な実力を表しています。
- * Semiconductor products generally have characteristic variation.
- Typical is a statistical average of the device's ability.

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[Special applications]

Transportation equipment (vehicles, ships, etc.), trunk-line communication equipment, traffic signal control systems, anti-disaster/crime systems, safety equipment, medical equipment, etc.

[Specific applications]

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S25VB10 THRU S25VB100

桥式整流器 Bridge Rectifier

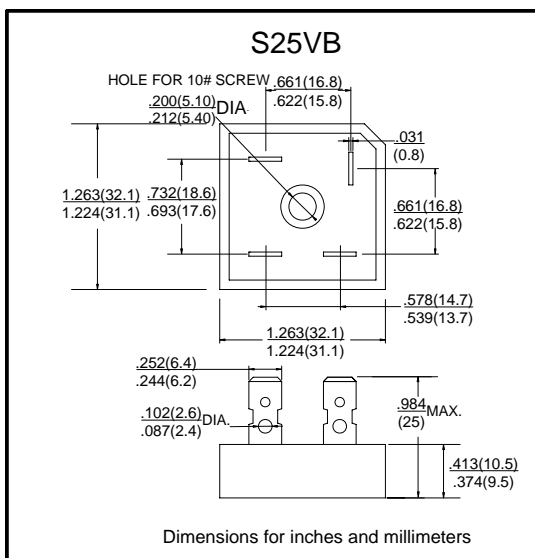
■特征 Features

- I_o 25A
- V_{RRM} 100V-1000V
- 玻璃钝化芯片
Glass passivated chip
- 耐正向浪涌电流能力高
High surge forward current capability

■用途 Applications

- 作一般电源单相桥式整流用
General purpose 1 phase Bridge rectifier applications

■外形尺寸和印记 Outline Dimensions and Mark



■极限值（绝对最大额定值）

Limiting Values (Absolute Maximum Rating)

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions	S25VB					
				10	20	40	60	80	100
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		100	200	400	600	800	1000
平均整流输出电流 Average Rectified Output Current	I_o	A	60Hz正弦波, 电阻负载 60Hz sine wave, R-load	用散热器 $T_c=85^\circ\text{C}$ With heatsink $T_c=85^\circ\text{C}$	25				
				无散热器 $T_a=40^\circ\text{C}$ Without heatsink $T_a=40^\circ\text{C}$	6				
正向（不重复）浪涌电流 Surge(Non-repetitive) Forward Current	I_{FSM}	A	60Hz正弦波, 一个周期, $T_a=25^\circ\text{C}$ 60Hz sine wave, 1 cycle, $T_a=25^\circ\text{C}$	400					
正向浪涌电流的平方对电流浪涌持续时间的积分值 Current Squared Time	I^2t	A^2S	$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$, 单个二极管 $1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$, Rating of per diode	660					
存储温度 Storage Temperature	T_{stg}	$^\circ\text{C}$		-40 ~ +150					
结温 Junction Temperature	T_j	$^\circ\text{C}$		-40 ~ +150					
绝缘耐压 Dielectric Strength	V_{dis}	KV	端子与外壳之间外加交流电, 一分钟 Terminals to case, AC 1 minute	2.5					

■电特性（ $T_a=25^\circ\text{C}$ 除非另有规定）

Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition	最大值 Max
正向峰值电压 Peak Forward Voltage	V_{FM}	V	$I_{FM}=12.5\text{A}$, 脉冲测试, 单个二极管的额定值 $I_{FM}=12.5\text{A}$, Pulse measurement, Rating of per	1.05
反向峰值电流 Peak Reverse Current	I_{RRM}	μA	$V_{RM}=V_{RRM}$, 脉冲测试, 单个二极管的额定值 $V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode	10
热阻 Thermal Resistance	$R_{\theta J-C}$	$^\circ\text{C}/\text{W}$	结和管壳之间 Between junction and case	1.5

■特性曲线（典型） Characteristics(Typical)

图1: I_o - T_a 曲线
FIG1: I_o - T_a Curve

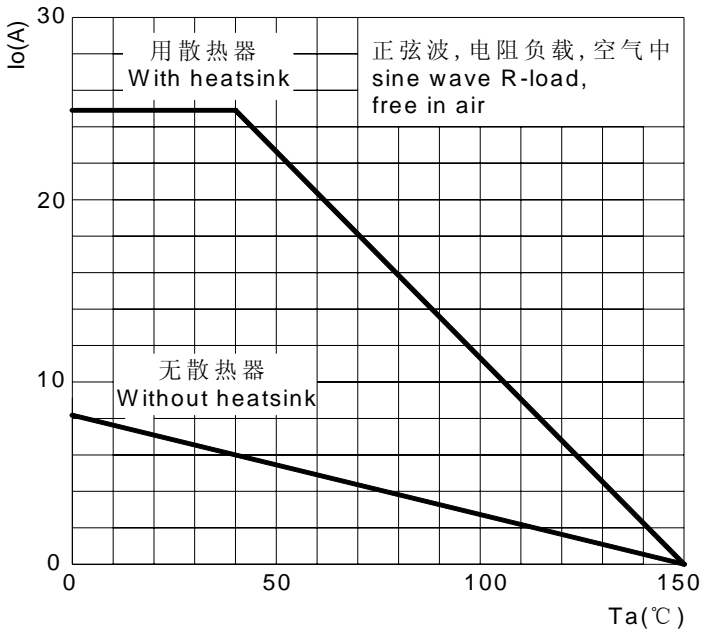


图2: 耐正向浪涌电流曲线
FIG2: Surge Forward Current Capadility

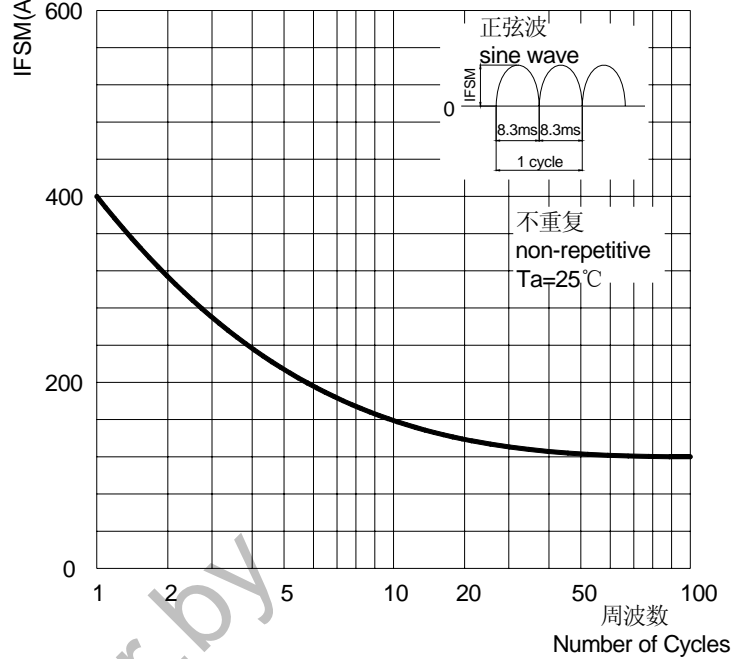


图3: 正向电压曲线
FIG3: Instantaneous Forward Voltage

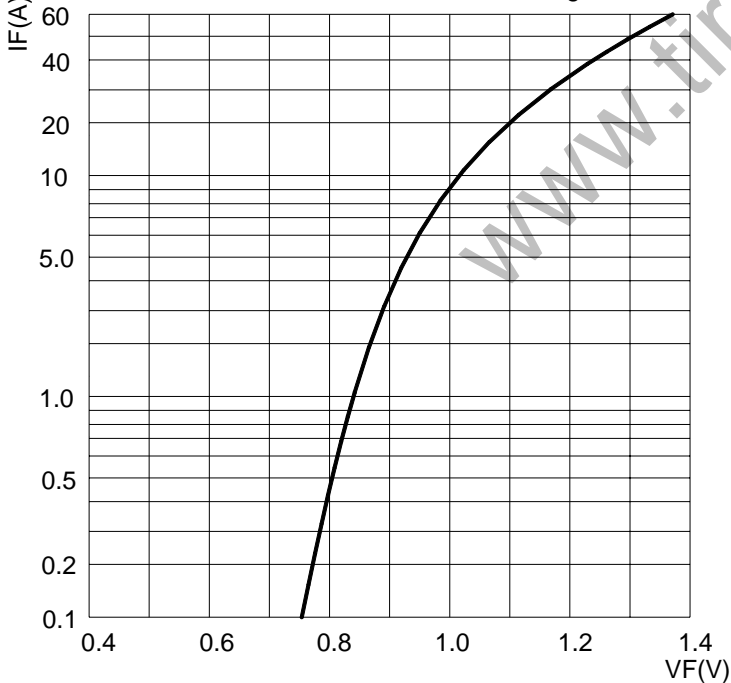
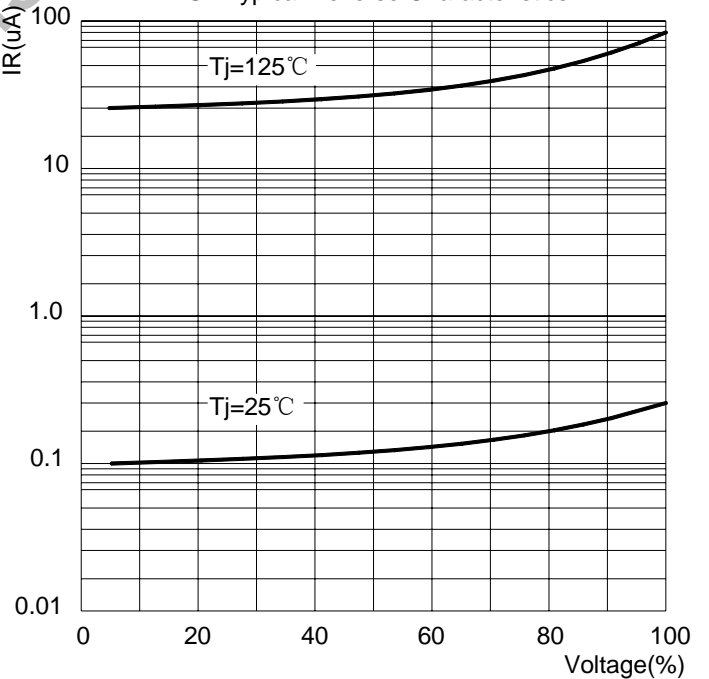


图4: 反向电流曲线
FIG4: Typical Reverse Characteristics



S25VB20 ~ S25VB60

PRV : 200 ~ 600 Volts

Io : 25 Amperes

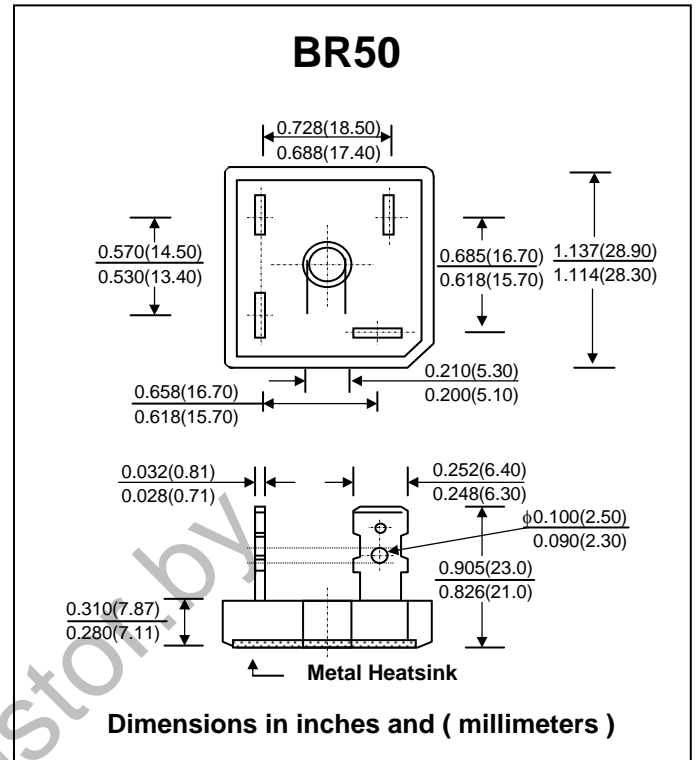
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : Molded plastic with heatsink integrally mounted in the bridge encapsulation
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : plated .25" (6.35 mm). Faston
- * Polarity : Polarity symbols marked on case
- * Mounting position : Bolt down on heat-sink with silicone thermal compound between bridge and mounting surface for maximum heat transfer efficiency.
- * Weight : 17.1 grams

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	S25VB20	S25VB60	UNIT
Maximum Reverse Voltage	V_{RM}	200	600	V
Maximum Average Forward Current $T_c = 85^\circ\text{C}$	$I_{F(AV)}$	25		A
Maximum Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	400		A
Current Squared Time at $1\text{ms} \leq t < 10\text{ms}$.	I^2t	800		A^2S
Maximum Forward Voltage per Diode at $I_F = 12.5\text{A}$	V_F	1.05		V
Maximum DC Reverse Current at $V_R = V_{RRM}$ (Pulse Measurement, Rating of per diode)	I_R	10		μA
Typical Thermal Resistance (Note 1)	$R_{\theta JC}$	1.5		$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	T_J	150		$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 40 to + 150		$^\circ\text{C}$

Note :
1. Thermal Resistance from junction to case with units mounted on a 5" x 6" x 4.9" (12.8cm.x 15.2cm.x 12.4cm.) Al.-Finned Plate

RATING AND CHARACTERISTIC CURVES (S25VB20 ~ S25VB60)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

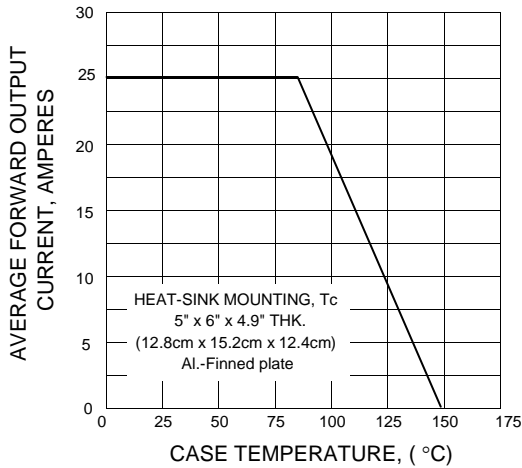


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

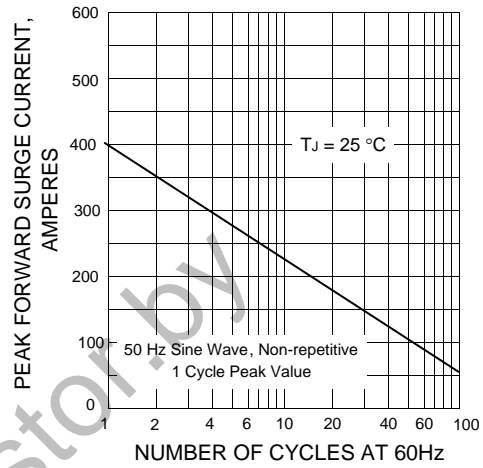


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

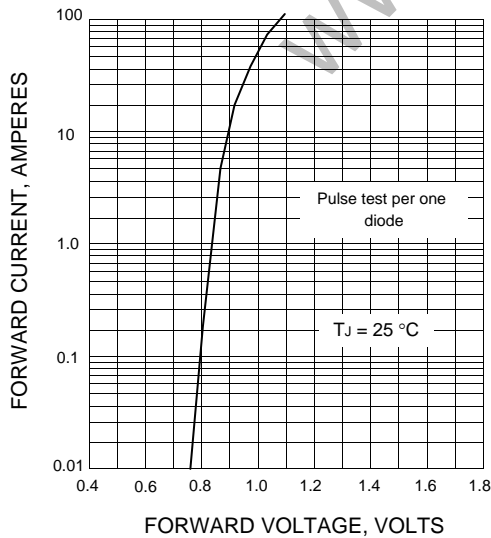
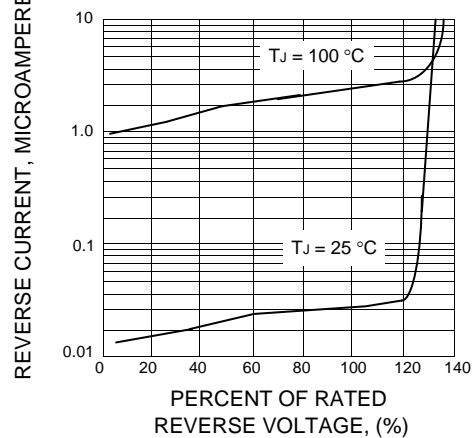


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE



S25VB005 THRU S25VB100

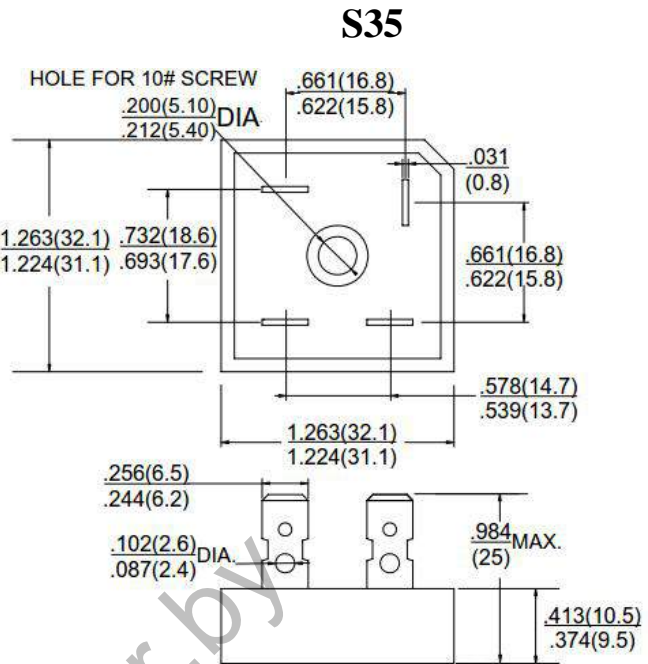
SINGLE-PHASE BRIDGE RECTIFIER GLASS PASSIVATED BRIDGE RECTIFIERS
 REVERSE VOLTAGE 50 to 1000 Volts FORWARD CURRENT 25 Ampere

FEATURES

- ◆ Rating to 1000V PRV
- ◆ High efficiency
- ◆ Glass passivated chip junction
- ◆ Electrically isolated metal case for maximum heat Dissipation
- ◆ The plastic material has UL flammability classification 94V-0
- ◆ Electrically isolated base-2500 Volts

Mechanical Data

- ◆ Case : Molded plastic with Heatsink internally mounted in the bridge encapsulation
- ◆ Polarity : As marked on Body
- ◆ Mounting : Hole for # 10 screw
- ◆ Weight : 0.70 ounces , 20 grams (terminal)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

PARAMETER	SYMBOL	S25VB 005	S25VB 10	S25VB 20	S25VB 40	S25VB 60	S25VB 80	S25VB 100	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	v
Maximum RMS Voltage	V_{RRM}	35	70	140	280	420	560	700	v
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	v
Maximum Average Forward Rectified Current @ $T_c=T_a$	$I_{(AV)}$	25.0							A
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load	I_{FSM}	350							A
Maximum Forward Voltage at 12.5A DC	V_F	1.05							v
Maximum DC Reverse Current @ $T_j=25^\circ C$ at rated DC blocking voltage @ $T_j=125^\circ C$	I_R	5.0 500							μA
I^2t Rating for Fusing ($t < 8.3ms$)	I^2t	370							A^2S
Typical Junction Capacitance per element (Note 2)	C_J	150							pF
Typical Thermal Resistance	$R_{\theta JC}$	1.4							$^\circ C/W$
Operating Temperature Range	T_J	-55 to +150							$^\circ C$
Storage Temperature Range	T_{STG}	-55 to +150							$^\circ C$

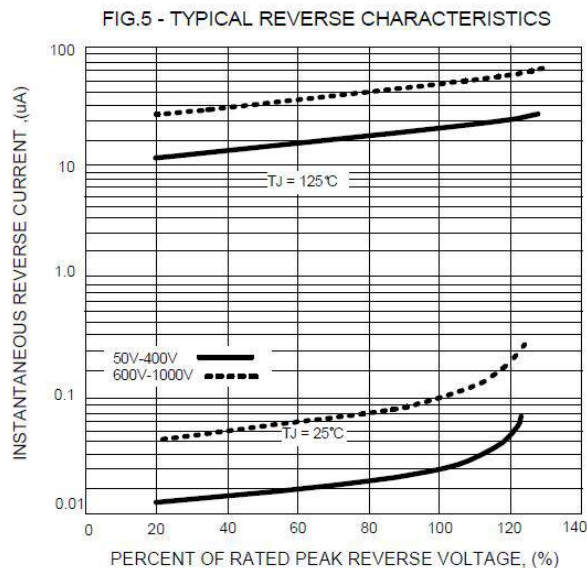
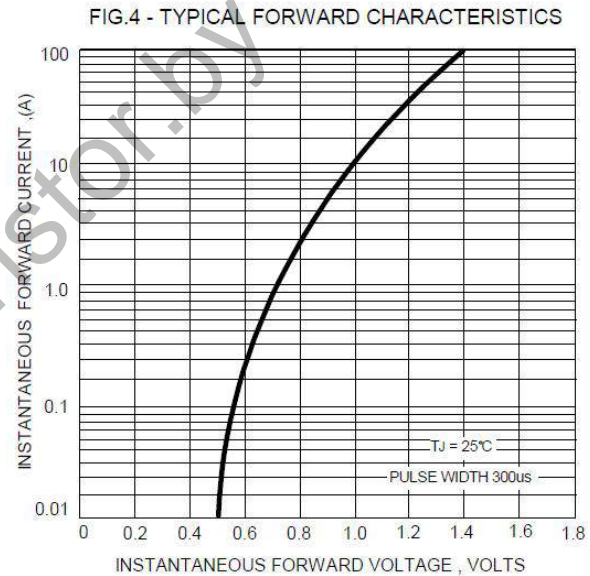
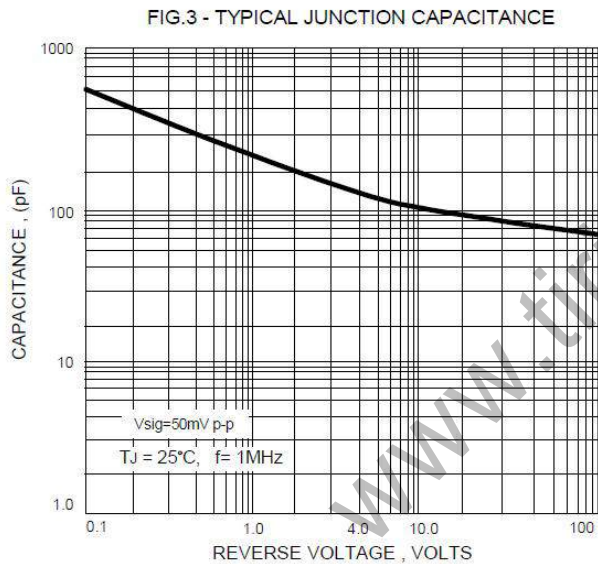
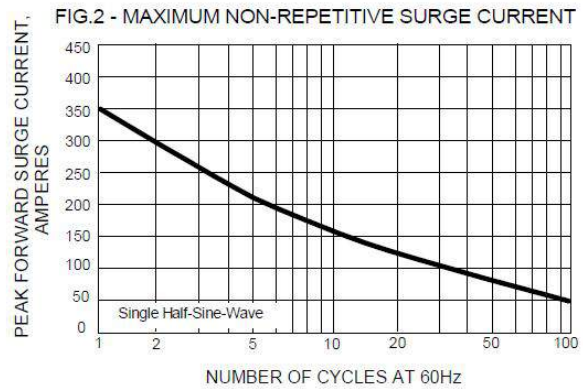
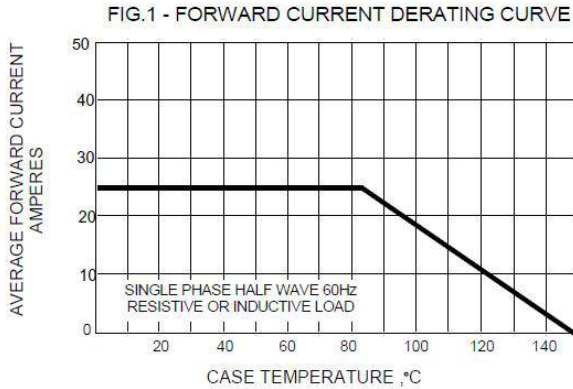
Note: 1. Measured at non-repetitive, for greater than 1ms and less than 8.3ms

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

S25VB005 THRU S25VB100

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RATING AND CHARACTERISTIC CURVES S25VB005 THRU S25VB100



Note: Specifications are subject to change without notice. For more detail and update, please visit our website.

 <p>Диодные мосты однофазные KBPC</p>	 <p>Диодные мосты однофазные QL</p>	 <p>Диодные мосты трёхфазные SQL</p>	 <p>Диодные мосты однофазные MDQ</p>
 <p>Диодные мосты трёхфазные MDE</p>	 <p>Диодные мосты однофазные DF10M</p>	<p>Минск www.fotorele.net www.tiristor.by email minsk17@tut.by tel.+375447584780 и другие, радиодетали, электронные компоненты каталог, описание, технические, характеристики, datasheet, параметры, маркировка, габариты, фото, аналог, замена, смотрите ниже</p>	



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